

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

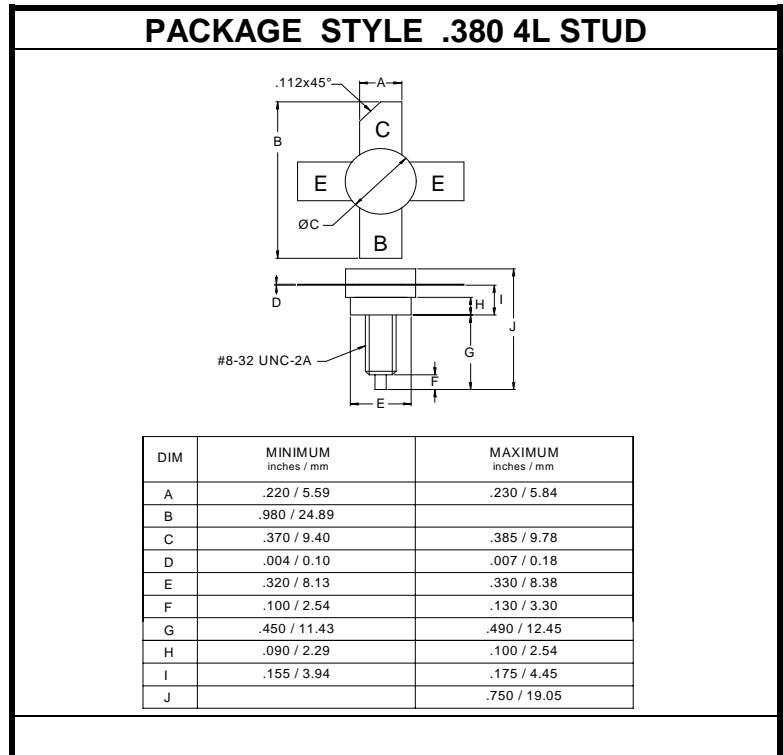
The **ASI PT9730** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 10$  dB at 10W/175 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CBO}$	60 V
$V_{CEO}$	35 V
$V_{CES}$	60 V
$V_{EBO}$	4.0 V
$P_{DISS}$	10 W @ $T = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	17.5 $^\circ\text{C/W}$


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 200$ mA	60			V
$BV_{CES}$	$I_C = 50$ mA	60			V
$BV_{CEO}$	$I_C = 100$ mA	35			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_{CE} = 25$ V			0.5	mA
$h_{FE}$	$V_{CE} = 10$ V $I_C = 500$ mA	20		150	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			12	pF
$P_G$ $\eta_C$	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 175$ MHz	13	60		dB %